

SCHEDULE AT A GLANCE: Wednesday

October 31, 2018

Start	End	Agenda Item
8:00 AM	5:00 PM	ITRW Meeting (Salon I,II,V, VI)
7:30 PM	9:30 PM	JEDEC Meeting (Salon III & IV)



MISSION

The International Technology Roadmap for Wide band-gap power semiconductors (ITRW) will provide reference, guidance and services to identify the future research and technology developments of wide band-gap power semiconductors and their application, and thereby provide a reliable and comprehensive view on the Strategic Research Agenda and Technology Roadmap.

SCHEDULE AT A GLANCE: WEDNESDAY

October 31, 2018

Continental-style breakfasts will be served at the Break Area closest to the Ballroom. The food is available from 7 am to 4 pm and cold beverages from 7 am to 5 pm daily.

Tutorial Sessions Location: **Salon III – IV**

Start	End	Agenda Item
9:00 AM	10:00 AM	Tutorial: “SiC Power Device Reliability” Donald A. Gajewski, <i>Wolfspeed</i>
10:00 AM	11:00 AM	Tutorial: “How to Design High Efficiency and High Density GaN Switching Power Supply” Qingyun Huang, <i>University of Texas at Austin</i>
11:00 AM	12:00 PM	Tutorial: “Developing High Power, Medium Voltage Silicon Carbide based Power Electronics” Jin Wang, <i>Ohio State University</i> , Mark J. Scott, <i>Miami University</i> , and Haiwei Cai, <i>Southeast University</i>
12:00 PM	1:30 PM	Lunch (Tutorials attendees only, GT Hotel Dining)
1:30 PM	2:30 PM	Tutorial: “Silicon Carbide Power Devices: Making the Transition From Silicon” Victor Veliadis, <i>PowerAmerica/North Carolina State University</i>
2:30 PM	3:30 PM	Tutorial: “Measurement and Analysis Method of Parasitic Capacitance and Inductance in Power Device and Power Electronic Circuit” Ryo Takeda, <i>Keysight Technologies</i>
3:30 PM	4:30 PM	Tutorial: “Advanced Power Module Packaging: from Design to Validation” Fang Luo, David Huitink, and Yarui Peng, <i>University of Arkansas</i>
4:30 PM	5:30 PM	Tutorial: “Emerging Ultra-Wide Band Gap (UWBG) Power Electronic Devices” Sriram Krishnamoorthy, <i>University of Utah</i>
6:00 PM	8:00 PM	Vendor Exhibits and Social Reception

SCHEDULE AT A GLANCE: THURSDAY

November 1, 2018

Continental-style breakfasts will be served at the Break Area closest to the Ballroom. The food is available from 7 am to 4 pm and cold beverages from 7 am to 5 pm daily.

Start	End	Agenda Item
8:00 AM	8:15 AM	Welcome Address Eric Persson, Infineon (Salon III – IV)
8:15 AM	8:45 AM	Keynote “WBG Power Electronics: Major Challenges and Potential Pathways for Commercialization JOHN SHEN, <i>Illinois Institute of Technology</i> (Salon III – IV)
8:45 AM	9:15 AM	Keynote “Challenges, Opportunities, and Applications for GaN-based Flying Capacitor Multi-Level Converters” ROBERT PILAWA-PODGURSKI, <i>University of California, Berkeley</i> (Salon III – IV)
9:15 AM	9:40 AM	Break Coffee, Tea, and Refreshments provided by JEDEC
9:45 AM	10:30 AM	Panel Session “Ask the Experts: GaN Reliability /Qualification Q and A” SANDEEP BAHL, <i>TI</i> KENICHIRO TANAKA, <i>Panasonic</i> SAMEH KHALIL, <i>Infineon Technologies</i> JAUME ROIG, <i>ON Semiconductor</i> RON BARR, <i>Transphorm</i> (Salon III – IV)
10:30 AM	11:15 AM	Panel Session “SiC MOSFET Reliability and Ruggedness: Present Status and Future Directions” ANANT AGARWAL, <i>The Ohio State University</i> AIVARS LELIS, <i>Army Research Laboratory</i> DON GAJEWSKI, <i>Wolfspeed</i> SUBHASHISH BHATTACHARYA, <i>North Carolina State University</i> BRIAN PEASLEE, <i>General Motors</i> (Salon III – IV)
11:15 AM	1:15 PM	Lunch (GT Hotel dining) Buffet provided by <i>Focused Test, Inc.</i>

SCHEDULE AT A GLANCE: THURSDAY

November 1, 2018

Start	End	Agenda Item		
1:15 PM	1:45 PM	<p>Keynote</p> <p>“DOE Advanced Manufacturing Office Programs on Wide-Bandgap Power Electronics”</p> <p>ALLEN HEFNER, <i>NIST and DOE Advanced Manufacturing Office</i></p> <p>(Salon III – IV)</p>		
1:45 PM	2:15 PM	<p>Keynote</p> <p>“Reliability of GaN Power Transistors”</p> <p>KENICHIRO TANAKA, <i>Panasonic Corporation</i></p> <p>(Salon III – IV)</p>		
2:15 PM	2:45 PM	<p>Keynote</p> <p>“GaN and SiC: How They Will Impact the Future of Power Electronics Industry”</p> <p>ANA VILLAMOR, <i>Yole Développement</i></p> <p>(Salon III – IV)</p>		
2:45 PM	3:15 PM	<p>Break/Session Setup Period</p> <p>Coffee, Tea, and Refreshments</p>		
3:15 PM	5:20 PM	Technical Session 1		
		<p>GaN Enabled Application and Hybrid Switches (Conference A)</p>	<p>GaN Reliability and Devices (Salon I-II)</p>	<p>SiC Device Fabrication and Reliability (Salon V – VI)</p>
6:00 PM	9:00 PM	<p>Conference Banquet and Poster Session</p> <p>(Grand Ballroom Foyer)</p>		

SCHEDULE AT A GLANCE: FRIDAY

November 2, 2018

Continental-style breakfasts will be served at the Break Area closest to the Ballroom. The food is available from 7 am to 4 pm and cold beverages from 7 am to 5 pm daily.

Start	End	Agenda Item		
8:00 AM	8:30 AM	Keynote “Switched Tank Converters – Leveraging the Benefits of GaN and SiC” DONG CAO, <i>North Dakota State University</i> (Salon III – IV)		
8:30 AM	9:00 AM	Keynote “Gate Drive and Protection Considerations in Applying SiC MOSFETs” LEON TOLBERT, <i>Oak Ridge National Laboratory</i> (Salon III – IV)		
9:00 AM	9:30 AM	Keynote “Achieving High Power Density Through GaN Power Devices” ALEX Q. HUANG, <i>University of Texas at Austin</i> (Salon III – IV)		
9:30 AM	10:00 AM	Break/Session Setup Period Coffee, Tea, and Refreshments		
10:00 AM	11:40 AM	Technical Session 2		
		GaN Device Characterization and Gate Drive (Conference A)	High Efficiency SiC-based Power Converters (Salon I-II)	SiC Device Characterization (Salon V-VI)
11:40 AM	1:00 PM	Lunch (GT Hotel Dining) Lunch provided by Texas Instruments (12:30 PM – 1:00 PM: Session Setup Period)		
1:00 PM	2:40 PM	Technical Session 3		
		GaN Soft switching and Multilevel Applications (Conference A)	GaN Device Integration and Performance (Salon I-II)	Practical Considerations in SiC-based Power Converters (Salon V-VI)
2:40 PM	3:00 PM	Break/Session Setup Period Coffee, Tea, and Refreshments provided by <i>SemiProbe</i>		

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3:00 PM	4:40 PM	Technical Session 4	
		GaN Power Module and Package (Conference A)	SiC Power Modules and Devices for High Performance Power Converters (Salon I-II)
4:40 PM	5:00 PM	Conference Wrap-up Maryam , <i>Georgia Tech</i>	

